International TOR Rectifier

Provisional Data Sheet HFA45HI120C

HEXFRED™ ULTRA FAST, SOFT RECOVERY DIODE 1200V, 28A

Major Ratings and Characteristics

Characteristics		Units
V _{br} (per leg)	1200	V
IF(AV)	28	Α
t _{rr} (per leg)	135	ns
Q _{rr} (per leg)	675	nC
IRRM (per leg)	10	Α
VF (per leg)	3.9	V

Description

International Rectifier's HFA45HI120C is a state of the art ultra fast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available.

With basic ratings of 1200 volts and 28 amps continuous current, the HFA45HI120C is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultra fast recovery time, the HEXFRED product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the th portion of recovery.

Features:

- Ultrafast Recovery
- Ultra Soft Recovery
- Very Low IRRMVery Low Q_{rr}
- Guáranteed Avalanche
- Specified at Operating Conditions
- Hermetic
- Electrically Isolated
- Ceramic Éyelets

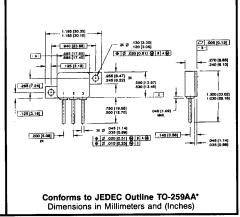
Benefits:

- Reduced RFI and EMI
- Reduced Power Loss in Diode and Switching Transistor
- Higher Frequency Operation
- Reduced Snubbing
- Reduced Parts Count

The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes.

The HEXFRED HFA45HI120C is ideally suited for applications in power supplies and power conversion systems (such as inverters, converters, UPS systems, and power factor correction circuits), motor drives, and many other similar applications where high speed, high efficiency rectification is needed.

CASE STYLE (ISOLATED BASE) ANODE COMMON AMODE CAINODE CALINODE Beryllia warning per MIL-PRF-19500 Packages containing beryllia shall not be ground, sandblasted, machined or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.



Voltage Ratings: T_J = 25 - 150°C

Parameter			Units	
V _{br} (per leg)	Max D.C. Reverse Voltage (V)	1200	v	
VISO (per leg)	Max PK Repetitive Reverse Voltage (V)	600		70K ft, I _R < 25μA

Absolute Maximum Ratings

Parameter		Min	Тур	Max	Units	Conditions
IF(AV)	Max Average Forward Current	_	-	28		$T_C = 100$ °C, d.c. = 50%, rect. wave $V_R = 0.8 V_{RRM}$
IFSM (per leg)	Max Single Pulse Forward Current	-	-	190	Α	T _C = 25°C, 1/2 Sine Wave, 60 Hz P.W. = 8,33 ms
IAS	Max Single Pulse Avalanche Current	-	-	14		L = 100 μH

Electrical Specifications: T_J = 25°C unless otherwise specified

Parameter		Min	Тур	Max	Units	Conditions
V _{FM} (per leg)	Max Forward Voltage	_	_	3.0	٧	IF = 14A
		_	_	3.9		IF = 28A
			_	2.7		IF = 14A, TJ = 125°C
I _{RM} (per leg)	Max Reverse Leakage Current	_ _	_	20	μA	V _R = V _R Rated
		_	_	2.0	mA	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ Rated
C _T (per leg)	Junction Capacitance		_	40	pF	V _R = 200V
LS	Internal Source Inductance	-	13	_	nH	Measured lead to lead 5mm from package body

Dynamic Recovery Specifications: T_J = 25°C unless otherwise specified

Parameter		Min	Тур	Max	Units	Conditions
trr (per leg)	Reverse Recovery Time	-	_	135	ns	IF = 14A, di/dt ≤ 200A/μs, VR = 200V
IRRM (per leg)	Max Reverse Recovery Current	-	_	10	Α	$I_F = 14A$, $di/dt \le 200A/\mu s$, $V_R = 200V$
QRR (per leg)	Reverse Recovered Charge	—	_	675	nC	IF = 14A, di/dt ≤ 200A/μs, VR = 200V

Thermal-Mechanical Specifications

Parameter		Min	Тур	Max	Units	Conditions
TJ, TSTG	Junction and Storage Temp Range	-55	_	150	•c	
$R_{\theta JC}$	Thermal Resistance; Junction to Case		_	1.20	K/W	
WT	Weight	I -	10.9	_	g	
Case	TO-259AA	_	JE	DEC		